# 74AHC1G125; 74AHCT1G125

Bus buffer/line driver; 3-state

Rev. 07 — 5 July 2007

**Product data sheet** 

## 1. General description

74AHC1G125 and 74AHCT1G125 are high-speed Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input ( $\overline{\text{OE}}$ ). A HIGH at  $\overline{\text{OE}}$  causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- ESD protection:
  - ◆ HBM JESD22-A114E: exceeds 2000 V
  - ◆ MM JESD22-A115-A: exceeds 200 V
  - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

## 3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AHC1G125GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1				
74AHCT1G125GW			5 leads; body width 1.25 mm					
74AHC1G125GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74AHCT1G125GV								

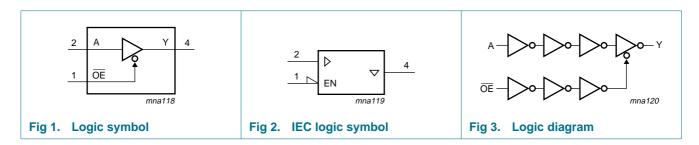


## 4. Marking

Table 2. Marking codes

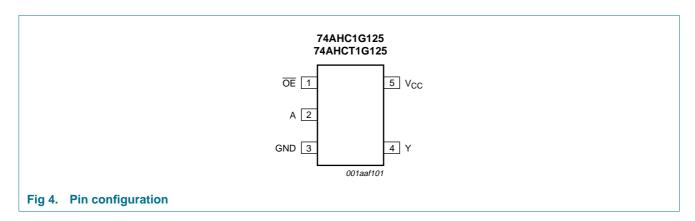
Type number	Marking
74AHC1G125GW	AM
74AHC1G125GV	A25
74AHCT1G125GW	CM
74AHCT1G125GV	C25

## 5. Functional diagram



## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
ŌĒ	1	data input
A	2	data input
GND	3	ground (0 V)
Υ	4	data output
$V_{CC}$	5	supply voltage

3 of 13

## 7. Functional description

### Table 4. Function table

 $H = HIGH \text{ voltage level}; L = LOW \text{ voltage level}; X = don't care; Z = high-impedance OFF-state}$ 

Inputs OE	Output	
ŌĒ	Α	Υ
L	L	L
L	Н	Н
Н	X	Z

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Cumbal	Davamatav	Canditiana	R#:	May	11!4
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$V_{I}$	input voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_1 < -0.5 \text{ V}$	-20	-	mA
I <sub>OK</sub>	output clamping current	$V_{O}$ < $-0.5$ V or $V_{O}$ > $V_{CC}$ + $0.5$ V	[1] _	±20	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I <sub>CC</sub>	supply current		-	75	mA
$I_{GND}$	ground current		<del>-</del> 75	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[2] _	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 9. Recommended operating conditions

### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	AHC1G1	25	74AHCT1G125			Unit
			Min	Тур	Max	Min	Тур	Max	
$V_{CC}$	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
$V_{I}$	input voltage		0	-	5.5	0	-	5.5	V
$V_{O}$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	-	-	-	ns/V
		$V_{CC}$ = 5.0 V $\pm$ 0.5 V	-	-	20	-	-	20	ns/V

<sup>[2]</sup> For both TSSOP5 and SC-74A packages: above 87.5  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K.

## 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G125							I		
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
$V_{OH}$	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = -50 \mu\text{A};  V_{CC} = 2.0 \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A$ ; $V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$ ; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}$ ; $V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A$ ; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	μΑ
II	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μΑ
Icc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF
For type	74AHCT1G125	5								
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
<b>U</b>	output voltage	$I_O = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V

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**Table 7. Static characteristics** ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
$I_{OZ}$	OFF-state output current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	0.25	-	2.5	-	10	μΑ
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = 3.4 \text{ V}$ ; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

## 11. Dynamic characteristics

 Table 8.
 Dynamic characteristics

 $GND = 0 \ V; \ t_f = t_f = \le 3.0 \ ns. \ For test circuit see Figure 7.$ 

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G12	5			'		'				
t <sub>pd</sub>	propagation	A to Y; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		$C_L = 15 pF$		-	4.7	8.0	1.0	9.5	1.0	11.5	ns
	$C_L = 50 pF$		-	6.6	11.5	1.0	13.0	1.0	14.5	ns	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		$C_L = 15 pF$		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50 pF$		-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t <sub>en</sub> en	enable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		$C_L = 15 pF$		-	5.0	8.0	1.0	9.5	1.0	11.5	ns
		$C_L = 50 pF$		-	6.9	11.5	1.0	13.0	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	<u>[3]</u>								
		$C_L = 15 pF$		-	3.6	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50 pF$		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
$t_{\text{dis}}$	disable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	<u>[2]</u>								
		$C_L = 15 pF$		-	6.0	9.7	1.0	11.5	1.0	12.5	ns
		$C_L = 50 pF$		-	8.3	13.2	1.0	15.0	1.0	16.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	<u>[3]</u>								
		$C_L = 15 pF$		-	4.1	6.8	1.0	8.0	1.0	8.5	ns
		$C_L = 50 pF$		-	5.7	8.8	1.0	10.0	1.0	11.0	ns

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V;  $t_r = t_f = \le 3.0$  ns. For test circuit see Figure 7.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C	to +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
$C_{PD}$	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$ ; $f = 1 \text{ MHz}$ ; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	9	-	-	-	-	-	pF
For type	74AHCT1G1	25									
t <sub>pd</sub>	propagation	A to Y; see Figure 5	<u>[1]</u>								
	delay	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		$C_L = 50 pF$		-	4.8	7.5	1.0	8.5	1.0	9.5	ns
t <sub>en</sub> er	enable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	3.9	5.1	1.0	6.0	1.0	6.5	ns
		$C_L = 50 pF$		-	5.1	7.5	1.0	8.5	1.0	9.5	ns
t <sub>dis</sub>	disable time	OE to Y; see Figure 6	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	4.5	6.8	1.0	8.0	1.0	8.5	ns
		C <sub>L</sub> = 50 pF		-	6.1	8.8	1.0	10.0	1.0	11.0	ns
$C_{PD}$	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$ ; $f = 1 \text{ MHz}$ ; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	11	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
  - $t_{\text{en}}$  is the same as  $t_{\text{PZL}}$  and  $t_{\text{PZH}}.$
  - $t_{\mbox{\scriptsize dis}}$  is the same as  $t_{\mbox{\scriptsize PLZ}}$  and  $t_{\mbox{\scriptsize PHZ}}.$
- [2] Typical values are measured at  $V_{CC}$  = 3.3 V.
- [3] Typical values are measured at  $V_{CC} = 5.0 \text{ V}$ .
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu W$ ).
  - $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:
  - $f_i$  = input frequency in MHz;
  - $f_o$  = output frequency in MHz;
  - $C_L$  = output load capacitance in pF;
  - V<sub>CC</sub> = supply voltage in Volts.

## 12. Waveforms

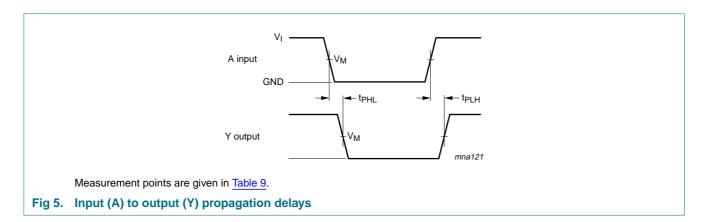
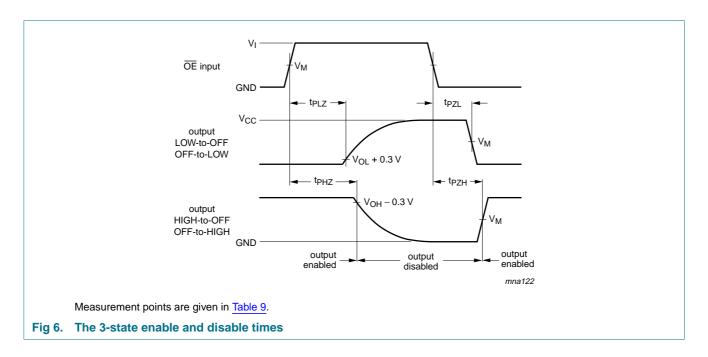
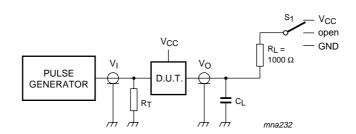


Table 9. Measurement point

Туре	Inputs		Output	
	V <sub>I</sub>	V <sub>M</sub>	V <sub>M</sub>	
74AHC1G125	GND to V <sub>CC</sub>	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	
74AHCT1G125	GND to 3.0 V	1.5 V	$0.5 \times V_{CC}$	





Test data is given in Table 8. Definitions for test circuit:

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_L$  = Load resistance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

For  $t_{PLH}$ ,  $t_{PHL}$ ,  $S_1 = open$ 

For  $t_{PLZ}$ ,  $t_{PZL}$ ,  $S_1 = V_{CC}$ 

For  $t_{PHZ}$ ,  $t_{PZH}$ ,  $S_1 = GND$ 

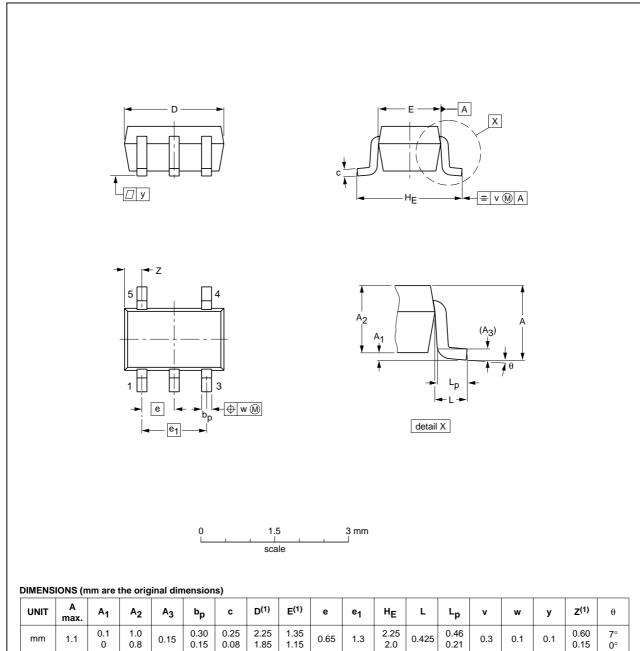
Fig 7. Load circuitry for switching times

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## 13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			<del>00-09-01</del> 03-02-19	

Fig 8. Package outline SOT353-1 (TSSOP5)

### Plastic surface-mounted package; 5 leads

**SOT753** 

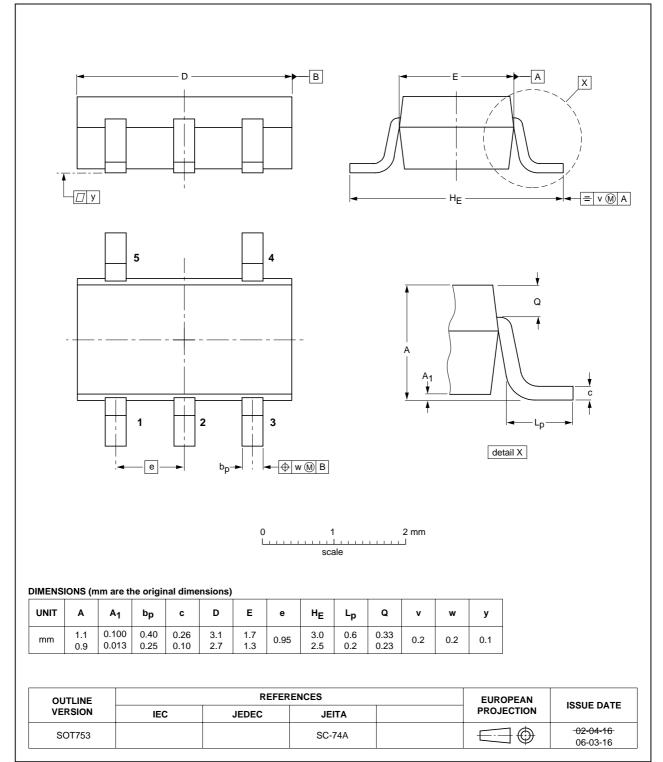


Fig 9. Package outline SOT753 (SC-74A)

## 14. Abbreviations

### Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G125_7	20070705	Product data sheet	-	74AHC_AHCT1G125_6
Modifications:		f this data sheet has been red NXP Semiconductors.	esigned to com	ply with the new identity
	<ul> <li>Legal texts h</li> </ul>	ave been adapted to the new of	company name	where appropriate.
	<ul> <li>Package SO</li> </ul>	T353 changed to SOT353-1 in	Section 3 and	Section 13.
	<ul> <li>Quick referer</li> </ul>	nce data and Soldering section	s removed.	
74AHC_AHCT1G125_6	20020606	Product specification	-	74AHC_AHCT1G125_5
74AHC_AHCT1G125_5	20020322	Product specification	-	74AHC_AHCT1G125_4
74AHC_AHCT1G125_4	20010222	Product specification	-	74AHC_AHCT1G125_3
74AHC_AHCT1G125_3	19990615	Product specification	-	74AHC_AHCT1G125_N_2
74AHC_AHCT1G125_N_2	19981207	Preliminary specification	-	74AHC_AHCT1G125_N_1
74AHC_AHCT1G125_N_1	19981125	Preliminary specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# 74AHC1G125; 74AHCT1G125

### **NXP Semiconductors**

Bus buffer/line driver; 3-state

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

